

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: A. KURAMATA et al.

Serial Number: 09/313,764

Filed: May 18, 1999

Group Art Unit: 2823

Examiner: W. Coleman

For: **OPTICAL SEMICONDUCTOR DEVICE HAVING AN EPITAXIAL LAYER OF III-V COMPOUND SEMICONDUCTOR MATERIAL CONTAINING N AS A GROUP V ELEMENT**



RECEIVED
AUG 30 2001

TECHNOLOGY CENTER 2800

AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

Date: August 27, 2001

Sir:

In response to the Office Action dated April 25, 2001, please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend claim 1 as follows:

1. (Amended) An optical semiconductor device, comprising:
 a substrate of SiC having a first conductivity type;
 a buffer layer of AlGaN formed on said substrate epitaxially, said buffer layer having said first conductivity type and a composition represented by a compositional parameter x as $\text{Al}_x\text{Ga}_{1-x}\text{N}$;